Applicant: Akio Iwabuchi et al. Serial No.: 10/566,421 Response Dated: July 21, 2008 Office Action Dated: June 23, 2008

Page 2 of 7

## **IN THE CLAIMS:**

Claim 1 (Withdrawn). A semiconductor device comprising: a first semiconductor region (15) of a first conductive type; a second semiconductor region (21) of a second conductive type formed on said first semiconductor region (15); a third semiconductor region (13) of the first conductive type formed in a surface region of said second semiconductor region (21) along an outer periphery of said second semiconductor region (21), and having a higher impurity concentration than that of said first semiconductor region (15); a fourth semiconductor region (14) of the first conductive type formed adjacent to a bottom surface of said third semiconductor region (13), and having a higher impurity concentration than that of said first semiconductor region (15); a fifth semiconductor region (19) of the first conductive type formed in the surface region of said second semiconductor region (21); a sixth semiconductor region (23) of the second conductive type formed in a surface region of said fifth semiconductor region (19); a first electrode (2) electrically connected to said second semiconductor region (21); a second electrode (4) electrically connected to said sixth semiconductor region (23); and a control electrode (3) laid out on said fifth semiconductor region (19) through an insulating film (31), wherein said fourth semiconductor region (14) is formed in said first semiconductor region (15) and said second semiconductor region (21), and is so formed as to extend closer to said fifth semiconductor region (19) than said third semiconductor region (13).

Claim 2 (Withdrawn). The semiconductor device according to claim 1, wherein said fourth semiconductor region (14) is formed in such a way that an electric potential difference between said control electrode (3) and said fifth semiconductor region (19) lying under said control electrode (3) becomes small with negative static electricity being applied to said first electrode (2).

Applicant: Akio Iwabuchi et al. Serial No.: 10/566,421

Response Dated: July 21, 2008

Office Action Dated: June 23, 2008

Page 3 of 7

Claim 3 (Withdrawn). The semiconductor device according to claim 1, wherein said

fourth semiconductor region (14) faces said fifth semiconductor region (19) through said

second semiconductor region (21).

Claim 4 (Withdrawn). The semiconductor device according to claim 1, wherein said

fourth semiconductor region (14) is so formed as to extend closer to said first electrode (2)

than said fifth semiconductor region (19).

Claim 5 (Withdrawn). The semiconductor device according to claim 1, further

comprising a seventh semiconductor region (22) of the second conductive type having a

higher impurity concentration than that of said second semiconductor region (21), in the

surface region of said second semiconductor region (21), wherein said seventh

semiconductor region (22) is electrically connected to said first electrode (2).

Claim 6 (Withdrawn). The semiconductor device according to claim 5, wherein said

fifth semiconductor region (19) is formed in a closed ring shape so as to surround said

seventh semiconductor region (22), and said third semiconductor region (13) is formed in a

closed ring shape so as to surround said fifth semiconductor region (19).

Claim 7 (Withdrawn). The semiconductor device according to claim 1, further

comprising an eighth semiconductor region (12) of the first conductive type formed in the

surface region of said fifth semiconductor region (19) and having a higher impurity

concentration than that of said fifth semiconductor region (19), wherein said eighth

semiconductor region (12) is electrically connected to a back gate electrode (5).

Claim 8 (Original). A semiconductor device comprising: a first semiconductor

region (15) of a first conductive type; a second semiconductor region (21) of a second

conductive type formed on said first semiconductor region (15); a third semiconductor region

(13) of the first conductive type formed in a surface region of said second semiconductor

Applicant: Akio Iwabuchi et al.

Serial No.: 10/566,421

Response Dated: July 21, 2008

Office Action Dated: June 23, 2008

Page 4 of 7

region (21) along an outer periphery of said second semiconductor region (21), and having a

higher impurity concentration than that of said first semiconductor region (15); a fourth

semiconductor region (14) of the first conductive type formed adjacent to a bottom surface of

said third semiconductor region (13), and having a higher impurity concentration than that of

said first semiconductor region (15); a fifth semiconductor region (19) of the first conductive

type formed in the surface region of said second semiconductor region (21); a sixth

semiconductor region (23) of the second conductive type formed in a surface region of said

fifth semiconductor region (19); a first electrode (2) electrically connected to said second

semiconductor region (21); a second electrode (4) electrically connected to said sixth

semiconductor region (23); and a control electrode (3) laid out on said fifth semiconductor

region (19) through an insulating film (31), wherein said fourth semiconductor region (14) is

formed in said first semiconductor region (15) and said second semiconductor region (21),

and has a protrusive piece (14a) so formed as to extend closer to said first electrode (2) side

than said third semiconductor region (13), and a portion (14b) so formed as not to extend

closer to said first electrode (2) than said protrusive piece (14a).

Claim 9 (Original). The semiconductor device according to claim 8, wherein the

protrusive piece (14a) of said fourth semiconductor region (14) is formed in such a way that

an electric potential difference between said control electrode (3) and said fifth

semiconductor region (19) lying under said control electrode (3) becomes small with

negative static electricity being applied to said first electrode (2).

Claim 10 (Original). The semiconductor device according to claim 8, wherein a top

surface of the protrusive piece (14a) of said fourth semiconductor region (14) faces a bottom

surface of said fifth semiconductor region (19) through said second semiconductor region

(21).

Claim 11 (Original). The semiconductor device according to claim 8, further

comprising a seventh semiconductor region (22) of the second conductive type having a

Applicant: Akio Iwabuchi et al.

Serial No.: 10/566,421

Response Dated: July 21, 2008 Office Action Dated: June 23, 2008

Page 5 of 7

higher impurity concentration than that of said second semiconductor region (21), in the

surface region of said second semiconductor region (21), wherein said seventh

semiconductor region (22) is electrically connected to said first electrode (2).

Claim 12 (Original). The semiconductor device according to claim 8, further

comprising an eighth semiconductor region (12) of the first conductive type formed in the

surface region of said fifth semiconductor region (19) and having a higher impurity

concentration than that of the fifth semiconductor region (19), wherein said eighth

semiconductor region (12) is electrically connected to a back gate electrode (5).

Claim 13 (Original). The semiconductor device according to claim 12, wherein said

fifth semiconductor region (19) has regions (19b) including said sixth semiconductor region

(23) and said eighth semiconductor region (12), and regions (19a) not including said sixth

semiconductor region (23) and said eighth semiconductor region (12), and both regions are

formed as to be alternately and apart from each other.

Claim 14 (Original). The semiconductor device according to claim 13, wherein the

protrusive piece (14a) of said fourth semiconductor region (14) is formed beneath said region

(19a) of said fifth semiconductor region (19) not including said sixth semiconductor region

(23) and said eighth semiconductor region (12).

Claim 15 (Original). The semiconductor device according to claim 14, wherein the

protrusive piece (14a) of said fourth semiconductor region (14) is so formed as to extend

closer to said first electrode (2) than said fifth semiconductor region (19).

Claim 16 (Original). The semiconductor device according to claim 13, wherein the

protrusive piece (14a) of said fourth semiconductor region (14) is not formed beneath said

region (19b) of said fifth semiconductor region (19) including said sixth semiconductor

region (23) and said eighth semiconductor region (12).

Applicant: Akio Iwabuchi et al.

Serial No.: 10/566,421

Response Dated: July 21, 2008

Office Action Dated: June 23, 2008

Page 6 of 7

Claim 17 (Original). The semiconductor device according to claim 13, wherein the

regions (19b) of said fifth semiconductor region (19), which include said sixth semiconductor

region (23) and said eighth region (12), and the regions (19a) of said fifth semiconductor

region (19) which do not include said sixth semiconductor region (23) and said eighth

semiconductor region (12) are laid out in said fifth semiconductor region (19) alternately and

apart from each other so as to surround said seventh semiconductor region (22), and said

third semiconductor region (13) is formed in a closed ring shape so as to surround said fifth

semiconductor region (19).

Claim 18 (Original). The semiconductor device according to claim 8, further

comprising a high-voltage resistive element (121).